

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-41.(Canceled)

42.(Currently Amended) A display device comprising:

a semiconductor substrate;

an insulating layer formed on the semiconductor substrate;

a switching transistor and a current controlling transistor formed on the insulating layer,
each comprising a source region, a drain region, a gate electrode and a gate insulating film;

an interlayer insulating film formed over the switching transistor and the current controlling transistor;

an electrode electrically connected with one of the source region and the drain region of the switching transistor, and formed over the interlayer insulating film;

a dielectric layer formed on the electrode;

a power supply line electrically connected with one of the source region and the drain region of the current controlling transistor, and formed on the dielectric layer;

a first electrode electrically connected with the other one of the source region and the drain region of the current controlling transistor;

an ~~organic~~ EL layer formed over the first electrode; and

a second electrode formed over the organic EL layer.

43.(Previously Presented) A display device according to claim 42, wherein the display device is incorporated in at least one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, an electronic book, a digital camera, and a DVD player.

44.(Previously Presented) A display device according to claim 42, wherein the first electrode overlaps the power supply line.

45.(Previously Presented) A display device according to claim 42, wherein the electrode comprises one selected from the group consisting of Al, Ta and Ti.

46.(Previously Presented) A display device according to claim 42, wherein the dielectric layer comprises an oxidation film of the electrode.

47.(Currently Amended) A display device comprising:

- a semiconductor substrate;
- an insulating layer formed on the semiconductor substrate;
- a p-channel type switching transistor and an n-channel type current controlling transistor formed on the insulating layer, each comprising a source region, a drain region, a gate electrode and a gate insulating film;
- an interlayer insulating film formed over the p-channel type switching transistor and the n-channel type current controlling transistor;

an electrode electrically connected with one of the source region and the drain region of the p-channel type switching transistor, and formed over the interlayer insulating film;

a dielectric layer formed on the electrode;

a power supply line electrically connected with one of the source region and the drain region of the n-channel type current controlling transistor, and formed on the dielectric layer;

a first electrode electrically connected with the other one of the source region and the drain region of the n-channel type current controlling transistor;

an ~~organic~~ EL layer formed over the first electrode; and

a second electrode formed over the organic EL layer.

48.(Previously Presented) A display device according to claim 47, wherein the first electrode overlaps the power supply line.

49.(Previously Presented) A display device according to claim 47, wherein the electrode comprises one selected from the group consisting of Al, Ta and Ti.

50.(Previously Presented) A display device according to claim 47, wherein the dielectric layer comprises an oxidation film of the electrode.

51.(Previously Presented) A display device according to claim 47, wherein the display device is incorporated in at least one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, an electronic book, a digital camera, and a DVD player.

52.(Currently Amended) A display device comprising:

- a semiconductor substrate;
- a switching transistor and a current controlling transistor formed on the semiconductor substrate, each comprising a source region, a drain region, a gate electrode and a gate insulating film;
- an interlayer insulating film formed over the switching transistor and the current controlling transistor;
- an electrode electrically connected with one of the source region and the drain region of the switching transistor, and formed over the interlayer insulating film;
- a dielectric layer formed on the electrode;
- a power supply line electrically connected with one of the source region and the drain region of the current controlling transistor, and formed on the dielectric layer;
- a first electrode electrically connected with the other one of the source region and the drain region of the current controlling transistor;
- an ~~organic~~ organic EL layer formed over the first electrode; and
- a second electrode formed over the organic EL layer.

53.(Previously Presented) A display device according to claim 52, wherein the first electrode overlaps the power supply line.

54.(Previously Presented) A display device according to claim 52, wherein the electrode comprises one selected from the group consisting of Al, Ta and Ti.

55.(Previously Presented) A display device according to claim 52, wherein the dielectric layer comprises an oxidation film of the electrode.

56.(Previously Presented) A display device according to claim 52, wherein the display device is incorporated in at least one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, an electronic book, a digital camera, and a DVD player.

57.(Currently Amended) A display device comprising:

- a semiconductor substrate;
- a p-channel type switching transistor and an n-channel type current controlling transistor formed on the semiconductor substrate, each comprising a source region, a drain region, a gate electrode and a gate insulating film;
- an interlayer insulating film formed over the p-channel type switching transistor and the n-channel type current controlling transistor;
- an electrode electrically connected with one of the source region and the drain region of

the p-channel type switching transistor, and formed over the interlayer insulating film;

a dielectric layer formed on the electrode;

a power supply line electrically connected with one of the source region and the drain region of the n-channel type current controlling transistor, and formed on the dielectric layer;

a first electrode electrically connected with the other one of the source region and the drain region of the n-channel type current controlling transistor;

an ~~organic~~ EL layer formed over the first electrode; and

a second electrode formed over the organic EL layer.

58.(Previously Presented) A display device according to claim 57, wherein the first electrode overlaps the power supply line.

59.(Previously Presented) A display device according to claim 57, wherein the electrode comprises one selected from the group consisting of Al, Ta and Ti.

60.(Previously Presented) A display device according to claim 57, wherein the dielectric layer comprises an oxidation film of the electrode.

61.(Previously Presented) A display device according to claim 57, wherein the display device is incorporated in at least one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, an electronic book, a digital camera, and a DVD player.

62.(Currently Amended) A display device comprising:

a semiconductor substrate;

a switching transistor and a current controlling transistor formed on the semiconductor substrate, each comprising a source region, a drain region, a gate electrode and a gate insulating film;

an interlayer insulating film formed over the switching transistor and the current controlling transistor;

an electrode electrically connected with one of the source region and the drain region of the switching transistor, and formed over the interlayer insulating film;

a dielectric layer formed on the electrode;

a power supply line electrically connected with one of the source region and the drain region of the current controlling transistor, and formed on the dielectric layer;

a storage capacitance comprising the electrode, the dielectric layer and the power supply line;

a first electrode electrically connected with the other one of the source region and the drain region of the current controlling transistor;

an ~~organic~~ EL layer formed over the first electrode; and

a second electrode formed over the organic EL layer.

63.(Previously Presented) A display device according to claim 62, wherein the first electrode overlaps the power supply line.

64.(Previously Presented) A display device according to claim 62, wherein the electrode comprises one selected from the group consisting of Al, Ta and Ti.

65.(Previously Presented) A display device according to claim 62, wherein the dielectric layer comprises an oxidation film of the electrode.

66.(Previously Presented) A display device according to claim 62, wherein the display device is incorporated in at least one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, an electronic book, a digital camera, and a DVD player.

67.(Currently Amended) A display device comprising:

a semiconductor substrate;

a p-channel type switching transistor and an n-channel type current controlling transistor formed on the semiconductor substrate, each comprising a source region, a drain region, a gate electrode and a gate insulating film;

an interlayer insulating film formed over the p-channel type switching transistor and the n-channel type current controlling transistor;

an electrode electrically connected with one of the source region and the drain region of the p-channel type switching transistor, and formed over the interlayer insulating film;

a dielectric layer formed on the electrode;

a power supply line electrically connected with one of the source region and the drain region of the n-channel type current controlling transistor, and formed on the dielectric layer;

a storage capacitance comprising the electrode, the dielectric layer and the power supply line;

a first electrode electrically connected with the other one of the source region and the drain region of the n-channel type current controlling transistor;

an ~~organic~~ EL layer formed over the first electrode; and

a second electrode formed over the organic EL layer.

68.(Previously Presented) A display device according to claim 67, wherein the first electrode overlaps the power supply line.

69.(Previously Presented) A display device according to claim 67, wherein the electrode comprises one selected from the group consisting of Al, Ta and Ti.

70.(Previously Presented) A display device according to claim 67, wherein the dielectric layer comprises an oxidation film of the electrode.

71.(Previously Presented) A display device according to claim 67, wherein the display device is incorporated in at least one selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a projector, an electronic book, a digital camera, and a DVD player.

72.(New) A display device according to claim 42, wherein the EL layer is organic.

73.(New) A display device according to claim 47, wherein the EL layer is organic.

74.(New) A display device according to claim 52, wherein the EL layer is organic.

75.(New) A display device according to claim 57, wherein the EL layer is organic.

76.(New) A display device according to claim 62, wherein the EL layer is organic.

77.(New) A display device according to claim 67, wherein the EL layer is organic.